



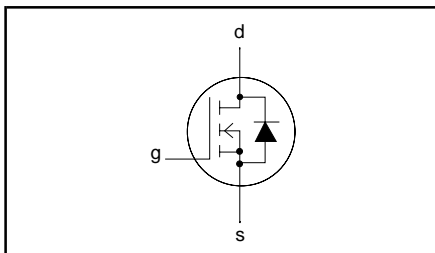
N-channel logic level TrenchMOS™ transistor

PSMN010-55D

FEATURES

- 'Trench' technology
- Very low on-state resistance
- Fast switching
- Logic level compatible

SYMBOL



QUICK REFERENCE DATA

$V_{DSS} = 55\text{ V}$
$I_D = 75\text{ A}$
$R_{DS(ON)} \leq 10.5\text{ m}\Omega (V_{GS} = 10\text{ V})$
$R_{DS(ON)} \leq 12\text{ m}\Omega (V_{GS} = 5\text{ V})$

GENERAL DESCRIPTION

SiliconMAX products use the latest Philips Trench technology to achieve the lowest possible on-state resistance in each package at each voltage rating.

Applications:-

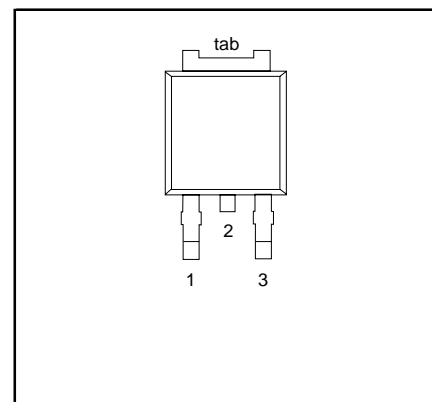
- d.c. to d.c. converters
- switched mode power supplies

The PSMN010-55D is supplied in the SOT428 (Dpak) surface mounting package.

PINNING

PIN	DESCRIPTION
1	gate
2	drain ¹
3	source
tab	drain

SOT428 (DPAK)



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DSS}	Drain-source voltage	$T_j = 25\text{ }^\circ\text{C to }175\text{ }^\circ\text{C}$	-	55	V
V_{DGR}	Drain-gate voltage	$T_j = 25\text{ }^\circ\text{C to }175\text{ }^\circ\text{C}; R_{GS} = 20\text{ k}\Omega$	-	55	V
V_{GS}	Continuous gate-source voltage		-	± 15	V
V_{GSM}	Peak pulsed gate-source voltage	$T_j \leq 150\text{ }^\circ\text{C}$	-	± 20	V
I_D	Continuous drain current	$T_{mb} = 25\text{ }^\circ\text{C}; V_{GS} = 5\text{ V}$ $T_{mb} = 100\text{ }^\circ\text{C}; V_{GS} = 5\text{ V}$	-	75^2	A
I_{DM}	Pulsed drain current	$T_{mb} = 25\text{ }^\circ\text{C}$	-	240	A
P_D	Total power dissipation	$T_{mb} = 25\text{ }^\circ\text{C}$	-	125	W
T_j, T_{stg}	Operating junction and storage temperature		-55	175	$^\circ\text{C}$

1 It is not possible to make connection to pin 2 of the SOT428 package.

2 Continuous current rating limited by package.



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AVALANCHE ENERGY LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
E_{AS}	Non-repetitive avalanche energy	Unclamped inductive load, $I_{AS} = 74$ A; $t_p = 100$ μ s; T_j prior to avalanche = 25°C; $V_{DD} \leq 25$ V; $R_{GS} = 50$ Ω ; $V_{GS} = 5$ V	-	264	mJ
I_{AS}	Non-repetitive avalanche current		-	75	A

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base		-	-	1.2	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	SOT428 package, pcb mounted, minimum footprint	-	50	-	K/W

ELECTRICAL CHARACTERISTICS $T_j = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0$ V; $I_D = 0.25$ mA; $T_j = -55^\circ\text{C}$	55 42	- -	- -	V V
$V_{GS(TO)}$	Gate threshold voltage	$V_{DS} = V_{GS}$; $I_D = 1$ mA $T_j = 175^\circ\text{C}$ $T_j = -55^\circ\text{C}$	1 0.5 -	1.5 - -	2 - 2.3	V V V
$R_{DS(ON)}$	Drain-source on-state resistance	$V_{GS} = 10$ V; $I_D = 25$ A $V_{GS} = 5$ V; $I_D = 25$ A $V_{GS} = 4.5$ V; $I_D = 25$ A $V_{GS} = 5$ V; $I_D = 25$ A; $T_j = 175^\circ\text{C}$	- - - -	7.4 8.6 9.1 -	10.5 12 13 25	m Ω m Ω m Ω m Ω
I_{GSS}	Gate source leakage current	$V_{GS} = \pm 10$ V; $V_{DS} = 0$ V	-	0.02	100	nA
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 25$ V; $V_{GS} = 0$ V; $T_j = 175^\circ\text{C}$	-	0.05	10 500	μ A μ A
$Q_{g(tot)}$	Total gate charge	$I_D = 75$ A; $V_{DD} = 44$ V; $V_{GS} = 5$ V	-	55	-	nC
Q_{gs}	Gate-source charge		-	13	-	nC
Q_{gd}	Gate-drain (Miller) charge		-	28	-	nC
$t_{d\ on}$	Turn-on delay time	$V_{DD} = 30$ V; $R_D = 1.2$ Ω ;	-	19	-	ns
t_r	Turn-on rise time	$V_{GS} = 10$ V; $R_G = 10$ Ω	-	114	-	ns
$t_{d\ off}$	Turn-off delay time	Resistive load	-	250	-	ns
t_f	Turn-off fall time		-	216	-	ns
L_d	Internal drain inductance	Measured tab to centre of die	-	3.5	-	nH
L_s	Internal source inductance	Measured from source lead to source bond pad	-	7.5	-	nH
C_{iss}	Input capacitance	$V_{GS} = 0$ V; $V_{DS} = 20$ V; $f = 1$ MHz	-	3300	-	pF
C_{oss}	Output capacitance		-	560	-	pF
C_{rss}	Feedback capacitance		-	370	-	pF

SiliconMAX

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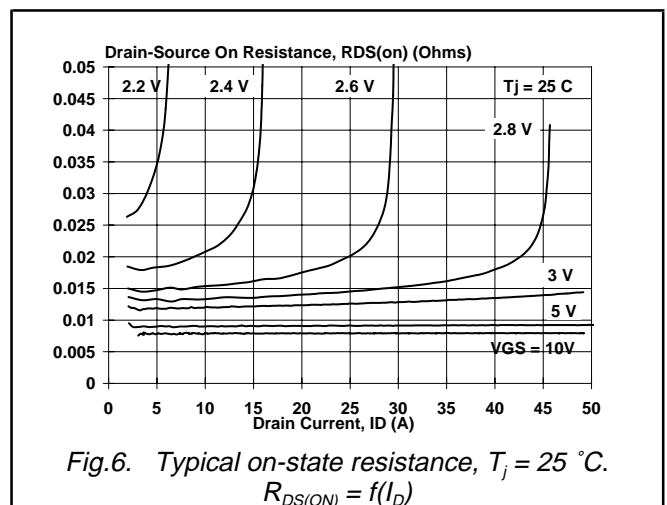
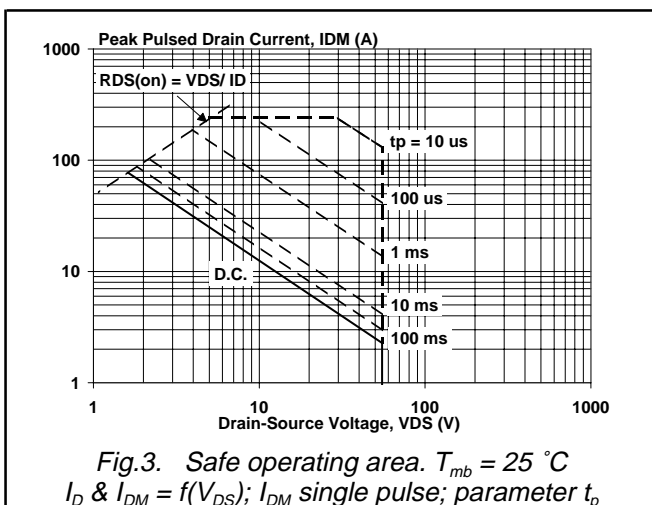
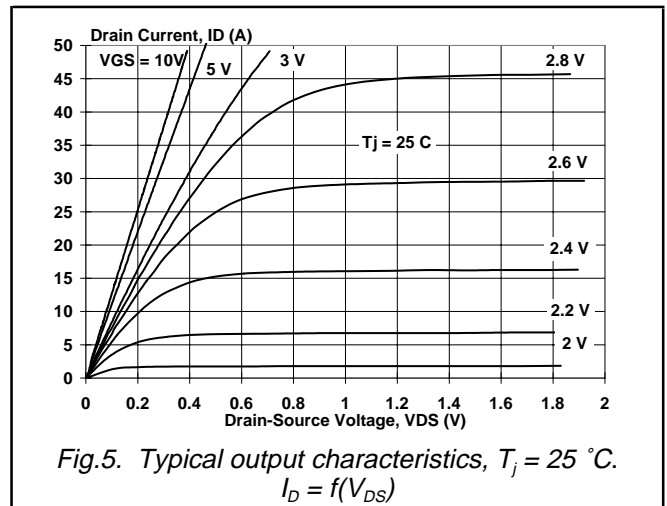
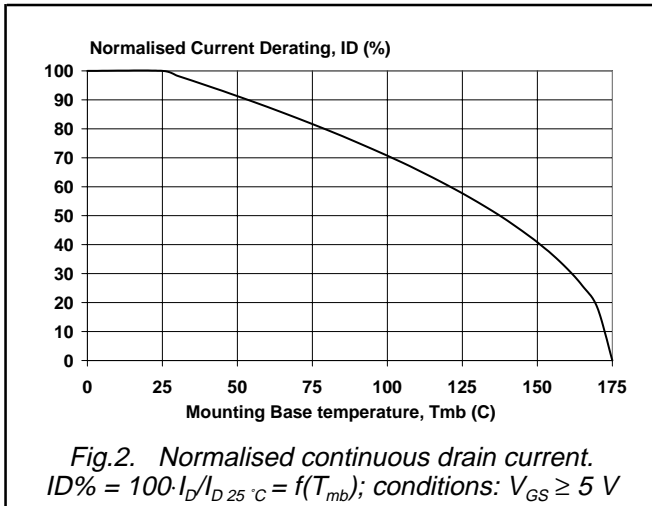
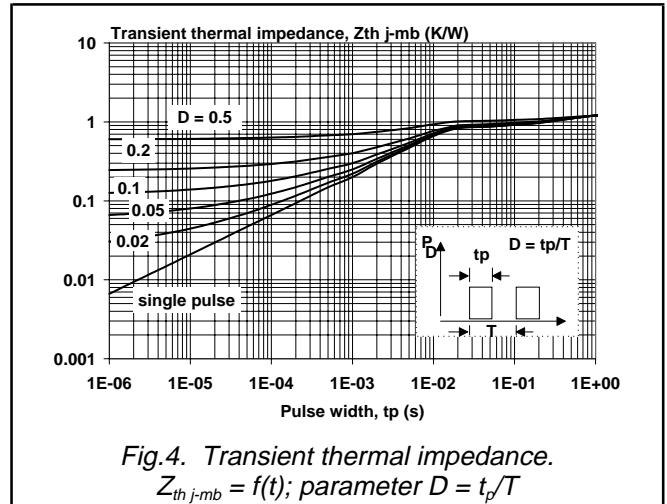
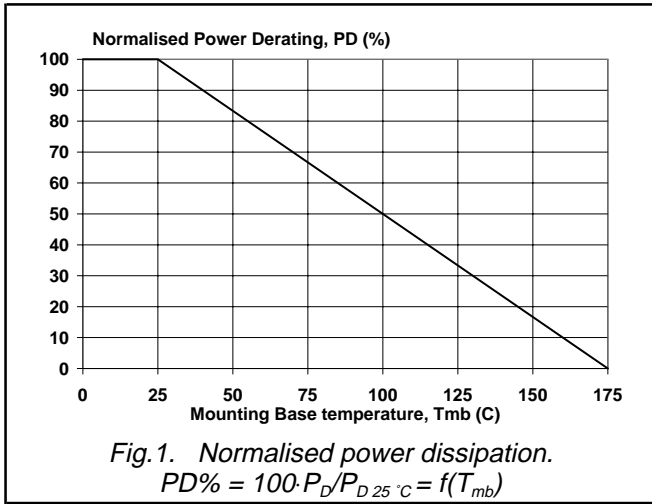
REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS $T_j = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_S	Continuous source current (body diode)		-	-	75	A
I_{SM}	Pulsed source current (body diode)		-	-	240	A
V_{SD}	Diode forward voltage	$I_F = 25\text{ A}; V_{GS} = 0\text{ V}$	-	0.95	1.2	V
t_{rr}	Reverse recovery time	$I_F = 25\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s};$	-	70	-	ns
Q_{rr}	Reverse recovery charge	$V_{GS} = 0\text{ V}; V_R = 25\text{ V}$	-	0.16	-	μC



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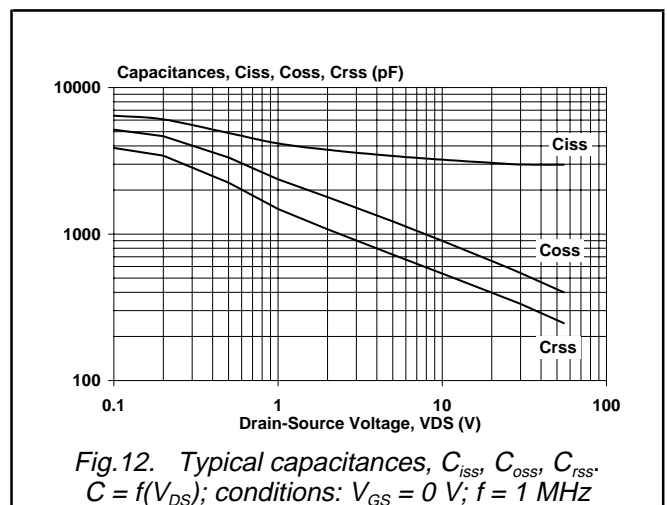
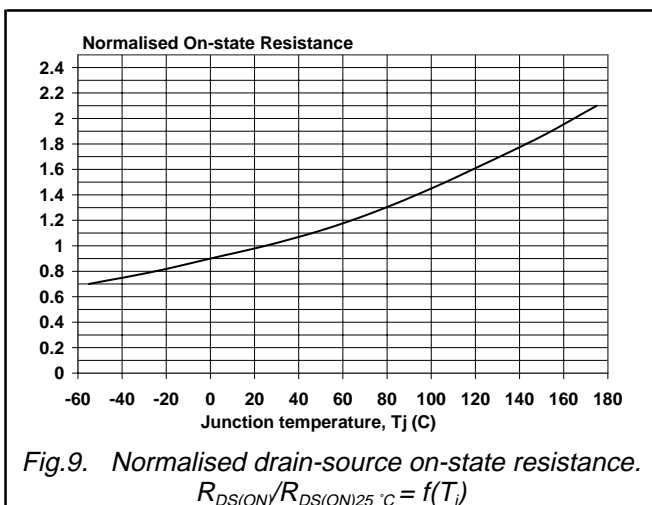
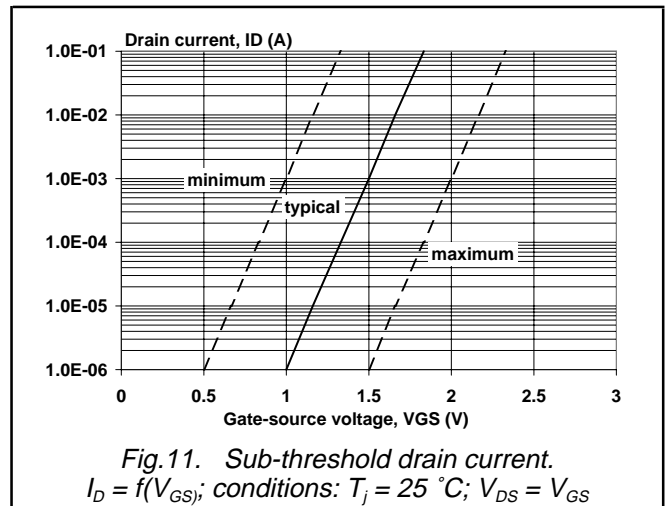
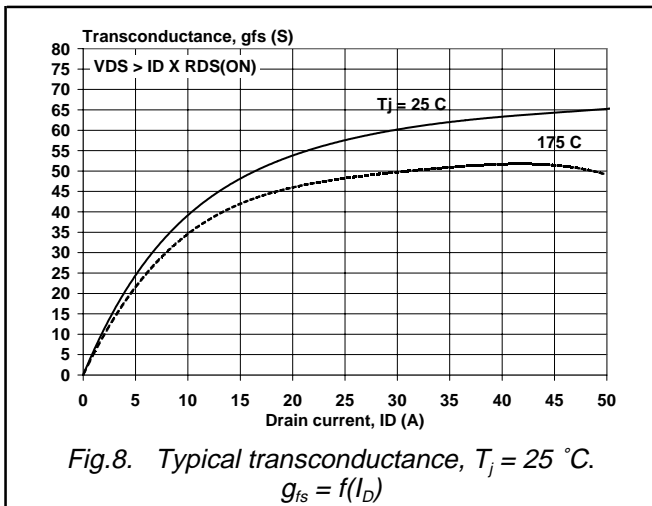
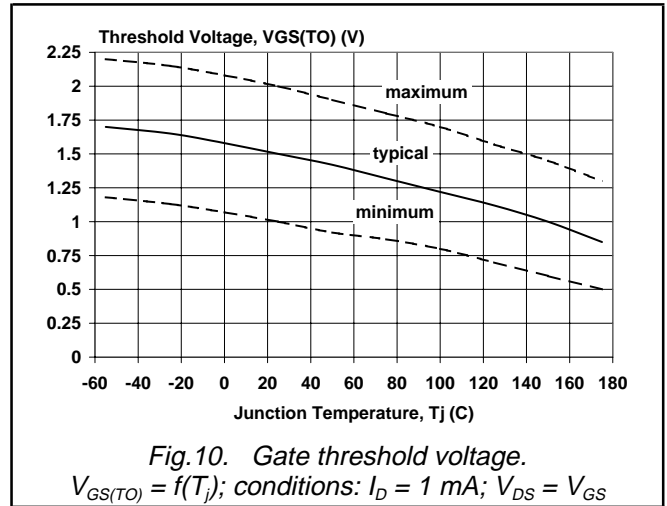
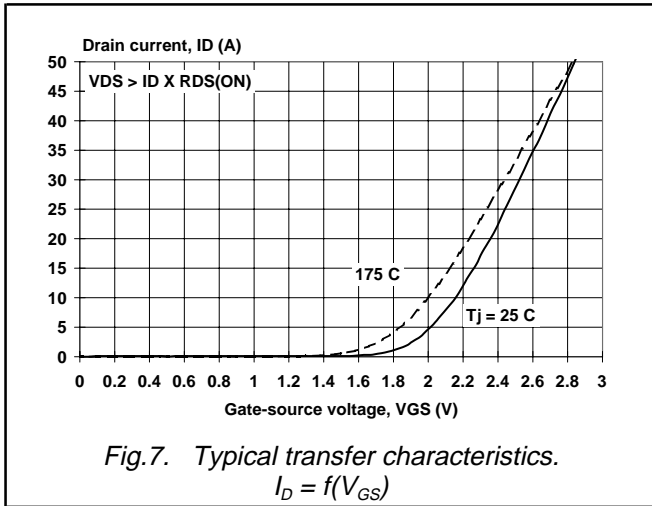
PSMN010-55D





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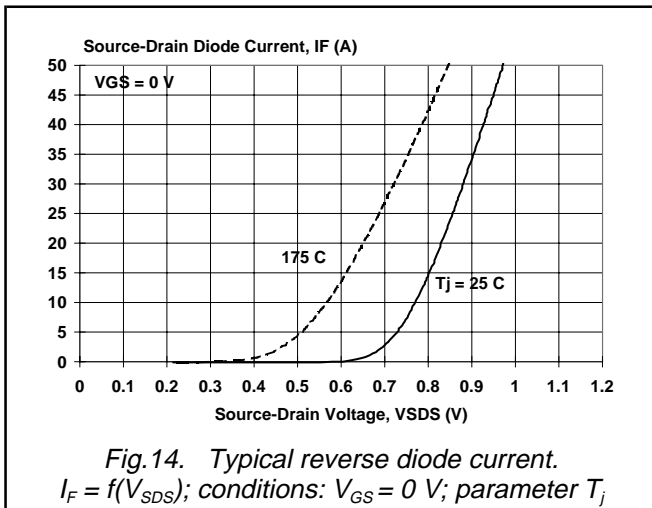
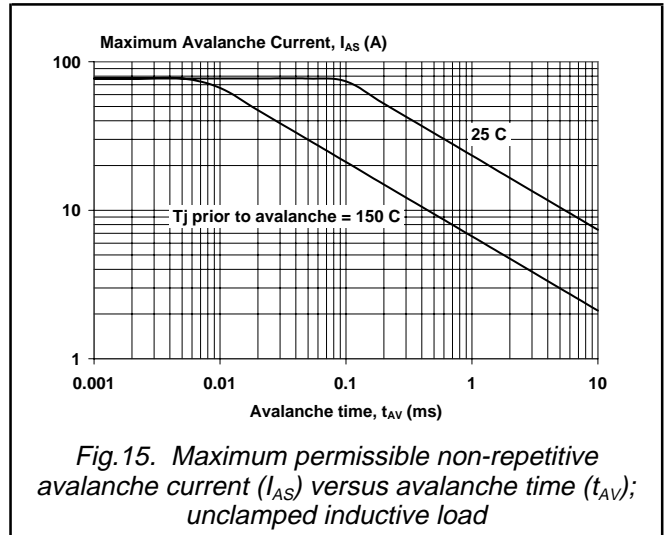
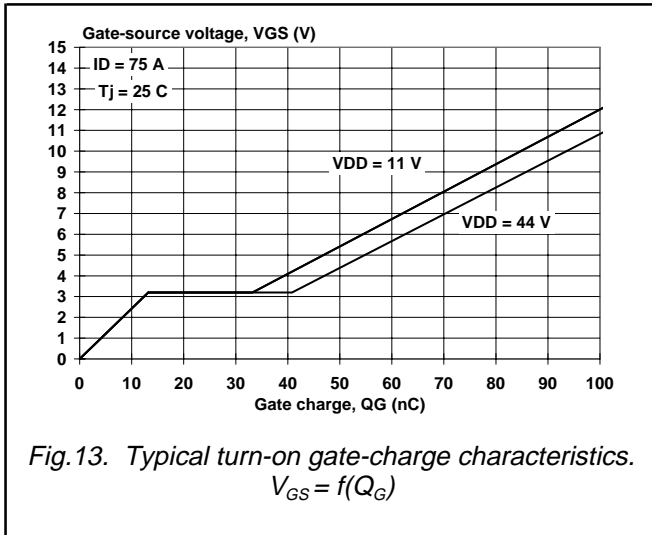
PSMN010-55D





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PSMN010-55D

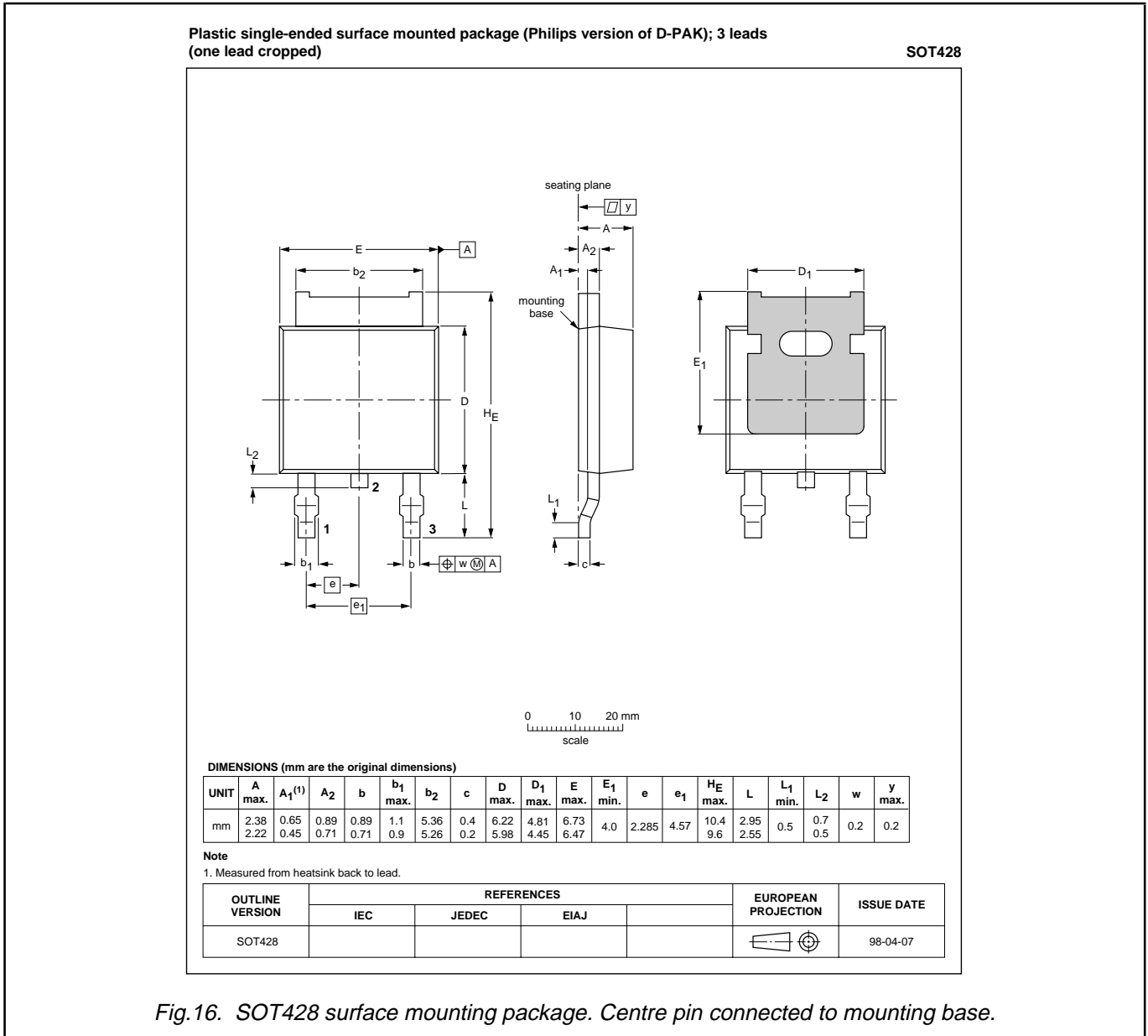




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PSMN010-55D

MECHANICAL DATA



Notes

1. This product is supplied in anti-static packaging. The gate-source input must be protected against static discharge during transport or handling.
2. Refer to SMD Footprint Design and Soldering Guidelines, Data Handbook SC18.
3. Epoxy meets UL94 V0 at 1/8".



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PSMN010-55D

MOUNTING INSTRUCTIONS

Dimensions in mm

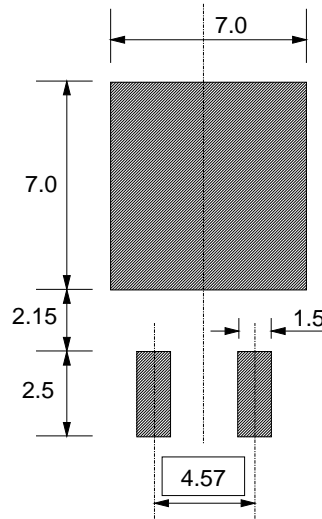


Fig.17. SOT428 : soldering pattern for surface mounting.



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PSMN010-55D

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	
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